

MMBTA05L, MMBTA06L

Driver Transistors

NPN Silicon



ON Semiconductor®

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Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

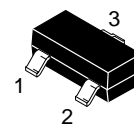
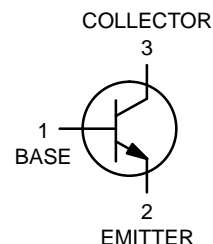
Rating	Symbol	Value	Unit
Collector–Emitter Voltage MMBTA05L MMBTA06L	V_{CEO}	60 80	Vdc
Collector–Base Voltage MMBTA05L MMBTA06L	V_{CBO}	60 80	Vdc
Emitter–Base Voltage	V_{EBO}	4.0	Vdc
Collector Current – Continuous	I_C	500	mAdc
Electrostatic Discharge	ESD	HBM Class 3B MM Class C CDM Class IV	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	–55 to +150	°C

1. FR–5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



**SOT-23
CASE 318
STYLE 6**

MARKING DIAGRAMS



MMBTA05LT1

MMBTA06LT1,
SMMBTA06L

1H, 1GM = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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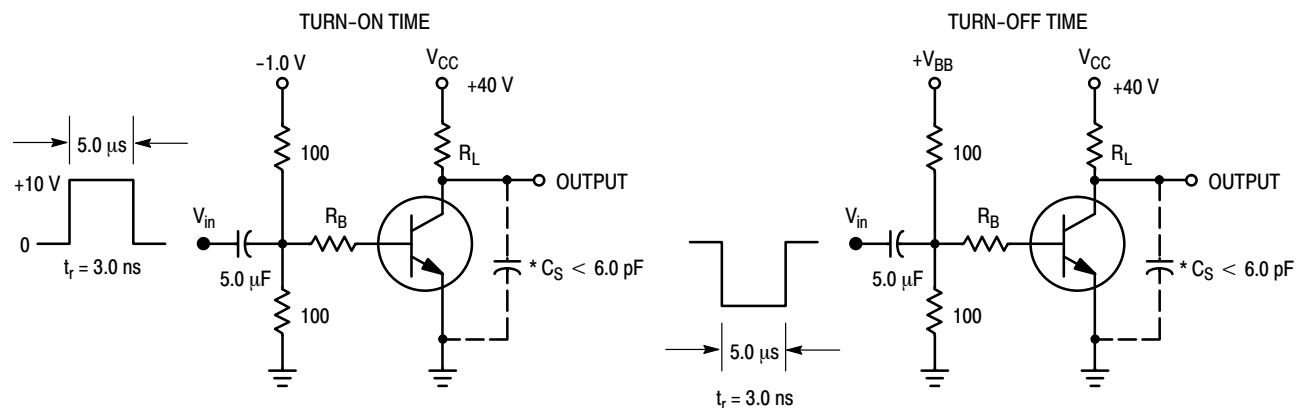
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 3) ($I_C = 1.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	60 80	–	Vdc
Emitter–Base Breakdown Voltage ($I_E = 100\ \mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	–	Vdc
Collector Cutoff Current ($V_{CE} = 60\text{ Vdc}$, $I_B = 0$)	I_{CES}	–	0.1	μA
Collector Cutoff Current ($V_{CB} = 60\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 80\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	0.1 0.1	μA
ON CHARACTERISTICS				
DC Current Gain ($I_C = 10\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$)	h_{FE}	100 100	–	–
Collector–Emitter Saturation Voltage ($I_C = 100\text{ mA}$, $I_B = 10\text{ mA}$)	$V_{CE(sat)}$	–	0.25	Vdc
Base–Emitter On Voltage ($I_C = 100\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$)	$V_{BE(on)}$	–	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current–Gain – Bandwidth Product (Note 4) ($I_C = 10\text{ mA}$, $V_{CE} = 2.0\text{ V}$, $f = 100\text{ MHz}$)	f_T	100	–	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



*Total Shunt Capacitance of Test Jig and Connectors
For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

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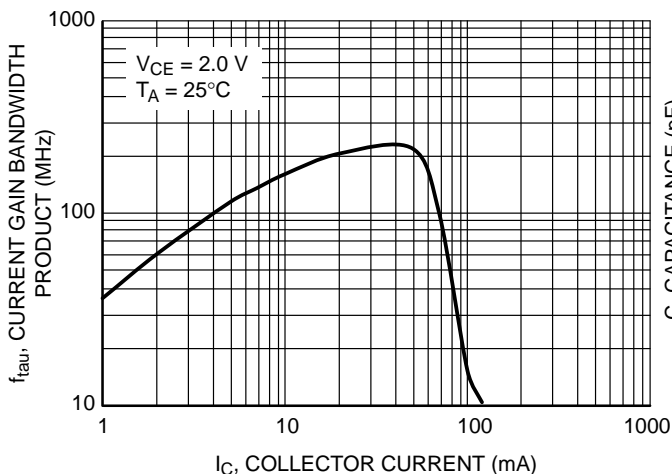


Figure 2. Current Gain Bandwidth Product vs. Collector Current

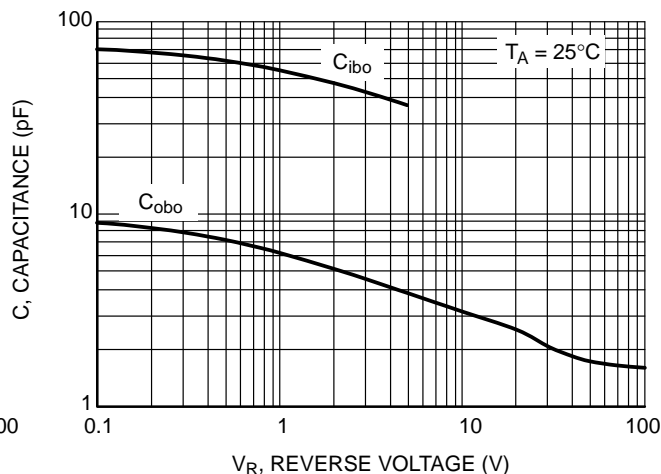


Figure 3. Capacitance

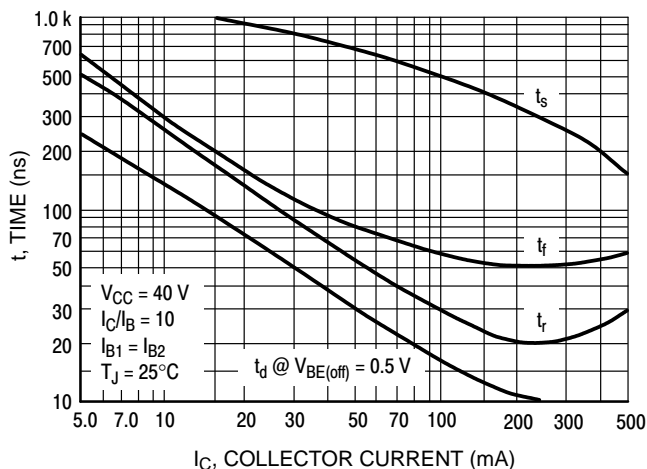


Figure 4. Switching Time

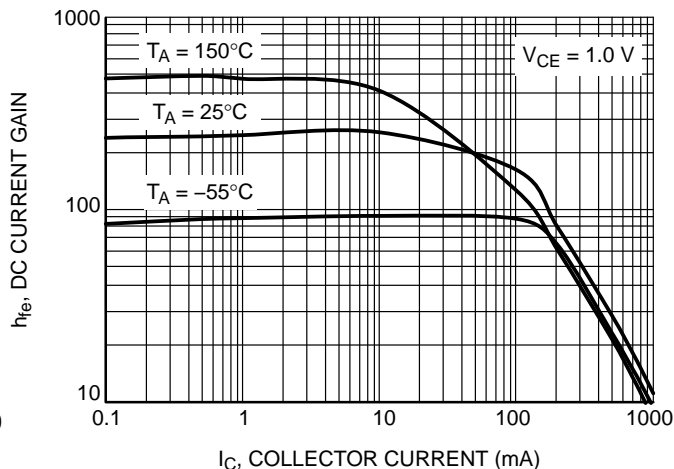


Figure 5. DC Current Gain vs. Collector Current

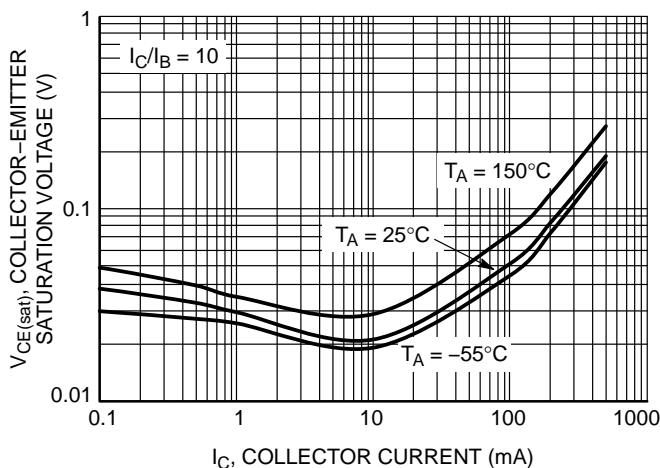


Figure 6. Collector Emitter Saturation Voltage vs. Collector Current

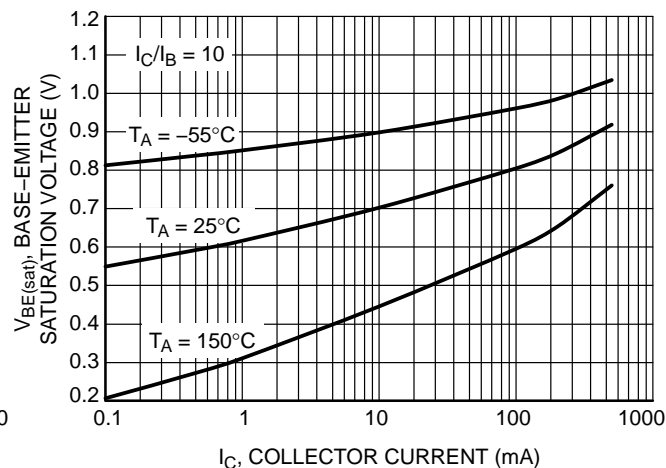


Figure 7. Base Emitter Saturation Voltage vs. Collector Current

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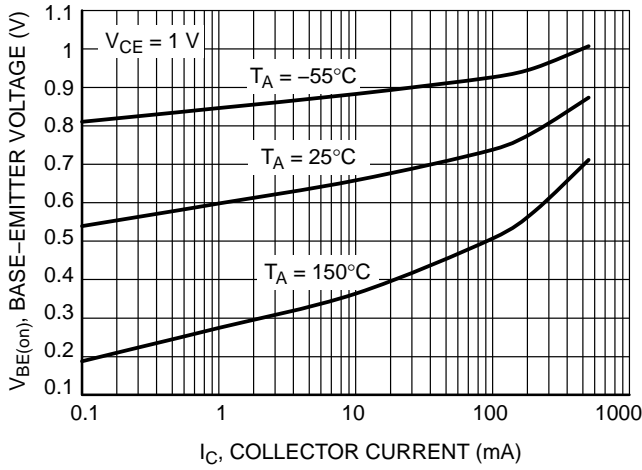


Figure 8. Base-Emitter Turn-ON Voltage vs. Collector Current

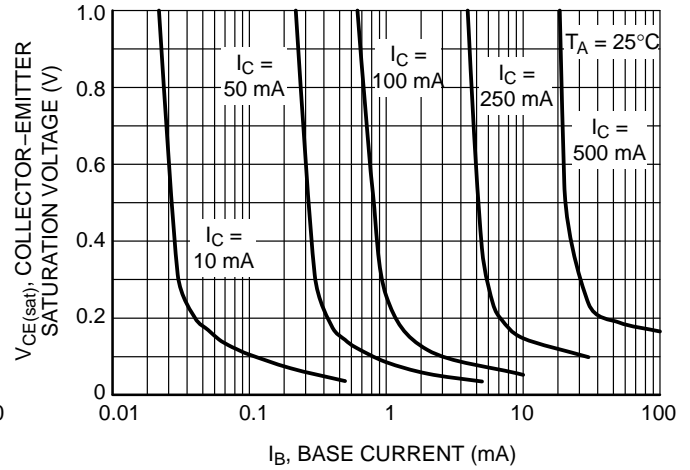


Figure 9. Saturation Region

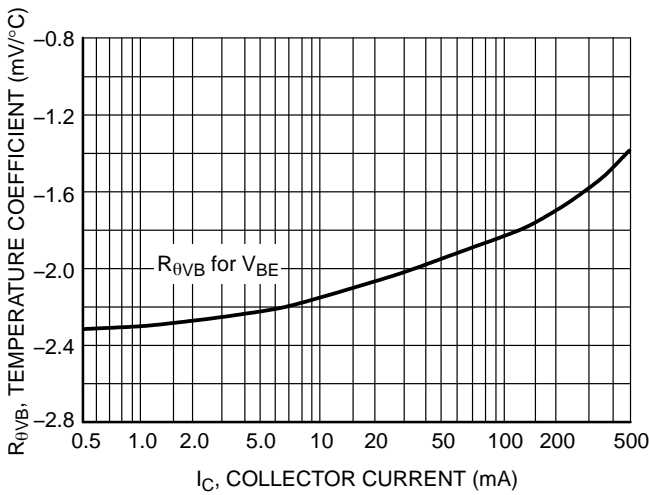


Figure 10. Base-Emitter Temperature Coefficient

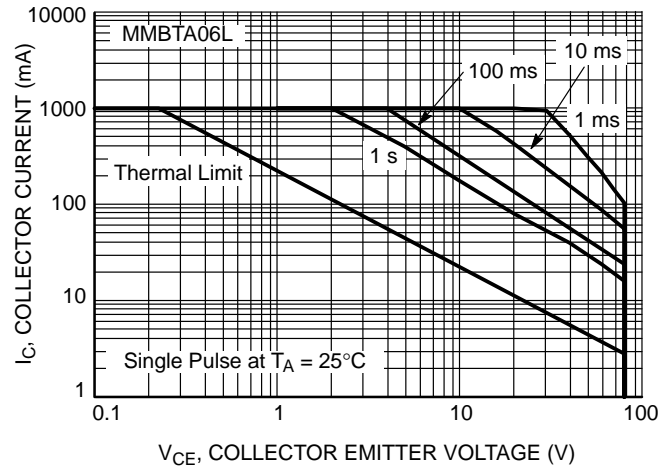


Figure 11. Safe Operating Area

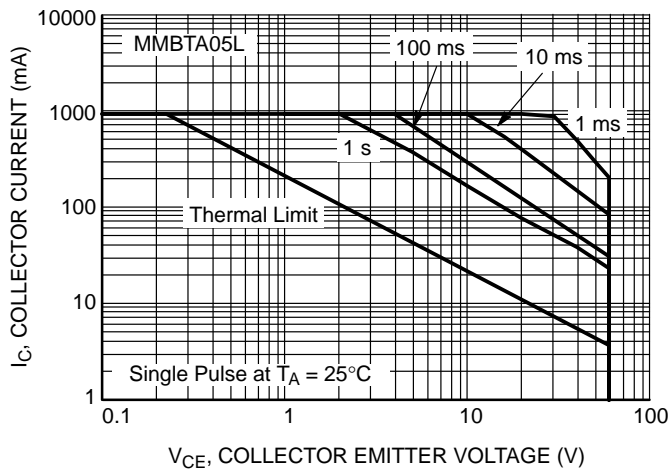


Figure 12. Safe Operating Area

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ORDERING INFORMATION

Device	Package	Shipping†
MMBTA05LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVMMBTA05LT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA05LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBTA06LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA06LT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA06LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBTA06LT3G*	SOT-23 (Pb-Free)	10,000 / Tape & Reel

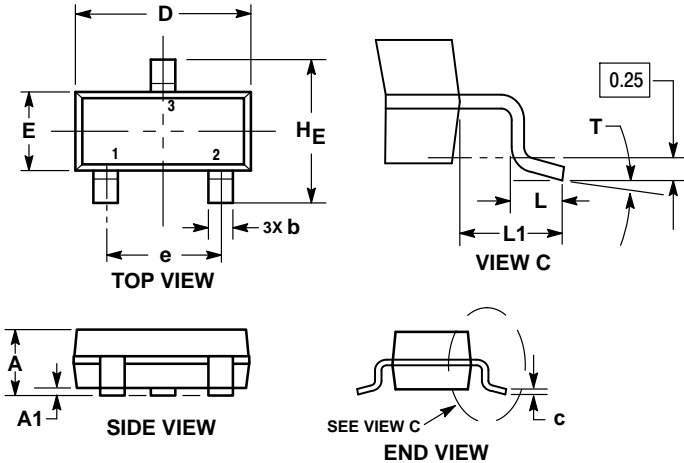
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

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PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AR

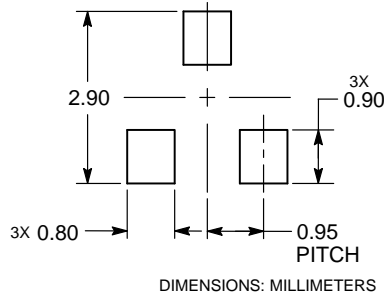


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

- STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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